What is claimed is:

1. A method, comprising:

forming a trench in a semiconductor substrate surface;

depositing a dielectric material onto the semiconductor substrate surface and into the trench;

implanting ions into at least some of the dielectric material to form an implanted dielectric region; and

polishing the semiconductor substrate surface to remove at least some of the implanted dielectric region.

2. The method of claim 1, wherein forming the trench comprises forming a barrier layer on the semiconductor substrate surface.

3. The method of claim 2, further comprising implanting ions into at least some of the barrier layer.

4. The method of claim 2, wherein implanting ions comprises implanting ions at least as deep as the barrier layer.

5. The method of claim 1, wherein the semiconductor substrate is a silicon wafer, and forming the trench comprises patterning a mask layer on a surface of the silicon wafer such that at least one region of the surface is exposed, and etching the trench in the exposed region.

6. The method of claim 1, wherein implanting ions comprises implanting silicon.

7. The method of claim 1, wherein implanting ions comprises implanting carbon.

8. The method of claim 1, wherein implanting ions comprises implanting oxygen.

9. The method of claim 1, wherein implanting ions comprises implanting nitrogen.

10. A method, comprising:

forming a nitride layer on a silicon wafer surface, the nitride layer having a first polish rate;

etching a plurality of recesses in the silicon wafer surface;

forming an oxide layer on the silicon wafer surface and in the plurality of recesses, the oxide layer having a second polish rate;

implanting ions into at least one of the nitride layer and the oxide layer to form an implanted region having a third polish rate different from the first and second polish rates; and

polishing the silicon wafer surface to remove at least some of the oxide layer and at least some of the implanted region therefrom.

11. The method of claim 10, wherein polishing comprises removing at least some of the nitride layer.

12. The method of claim 10, wherein polishing comprises chemical mechanical polishing.

13. The method of claim 10, wherein the ions are selected from the group consisting of silicon, carbon, nitrogen, and oxygen.

14. The method of claim 10, wherein implanting ions changes one of the first and second polish rates relative to the other polish rate.

15. An apparatus comprising:

a semiconductor substrate having a barrier layer formed thereon;

a trench etched into the substrate adjacent the barrier layer;

a dielectric layer deposited over the barrier layer and trench; and

a plurality of ions implanted into the dielectric layer.

16. The apparatus of claim 14 further comprising a plurality of ions implanted into the barrier layer.

17. The apparatus of claim 14 wherein the barrier layer comprises a silicon nitride layer.

18. The apparatus of claim 14 wherein the dielectric layer comprises a silicon oxide layer.

19. The apparatus of claim 14 wherein the dielectric layer is damaged by the plurality of implanted ions.

20. The apparatus of claim 14 wherein the plurality of ions are selected from the group consisting of silicon, carbon, nitrogen, and oxygen.